REMARKS

The claims have been amended to change dependencies and to re-number claims 10 to 13.

Entry of the above amendments is earnestly solicited. An early and favorable first action on the merits is earnestly solicited.

Attached hereto is a marked-up copy of the changes made to the application by this Amendment.

If necessary, the Commissioner is hereby authorized in this, concurrent, and future replies, to charge payment or credit any overpayment to Deposit Account No. 02-2448 for any additional fees required under 37 C.F.R. § 1.16 or under 37 C.F.R. § 1.17; particularly, extension of time fees.

Respectfully submitted,

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Attachment: Version with Markings Showing Changes Made

VERSION WITH MARKINGS TO SHOW CHANGES MADE

The claims have been amended as follows:

6. (Amended) The method of claim [6] 5, further comprising forming a mask on the semiconductor substrate such that the deep well areas are formed in the chip formation areas and not in the scribe lanes.

7. The semiconductor device of claim [1] 5, wherein, the first conductivity type is a p-type conductor; and the second conductivity type is a n-type conductor.

8. The semiconductor device of claim [6] 5, wherein, the first conductivity type is a n-type conductor; and the second conductivity type is a p-type conductor.

[10.] 9. The method of claim [6] 5, wherein a first conductive well area and a second conductive well area are separately formed within the deep well area.

[11.] 10. The method of claim [10] 9, wherein the first conductive well area is formed of the first conductivity type; and the second conductive well area is formed of the second conductivity type.

[12.] 11. The method of claim [6] 5, wherein the scribe lanes are formed at all portions surrounding the chip formation areas.

[13.] 12. The method of claim [7] 6, further comprising removing the mask using plasma processing or plasma equipment.